

IN THE CLAIMS

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1. (canceled)

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9. (currently amended) A method for fabricating a wire grid polarizer, comprising:  
depositing a wire grid material on a substrate, wherein the wire grid material comprises a dielectric material sandwiched between two metallic materials, wherein the dielectric and metallic materials act in concert to suppress reflection of rejected polarization;

depositing a resist film on the wire grid material;

bringing a mold with a wire grid pattern in contact with the resist film and compressing the mold and resist film together so as to emboss the wire grid pattern in the resist film; and

transferring the wire grid pattern in the resist film to the wire grid material on the substrate by etching.

10. (original) The method of claim 9, wherein the metallic materials are selected from the group consisting of Al, Au, Cr, Ir, Mo, Ni, Os, Pt, Rh, and W.

11. (original) The method of claim 9, wherein the dielectric material is selected from the group consisting of Si, SiO<sub>2</sub>, and GaAs.

12. (original) The method of claim 9, wherein the resist film comprises a thermoplastic polymer.

13. (original) The method of claim 12, further comprising heating the mold, the resist film and the substrate to a temperature above the glass transition temperature of the thermoplastic polymer prior to contacting the mold with the resist film.

14. (original) The method of claim 9, further comprising applying an anti-reflective coating on the substrate prior to depositing the wire grid material on the substrate.

15. (currently amended) The method of claim 9, wherein the substrate is made of a magneto-optical garnet material.

16. (currently amended) An integrated optical isolator, comprising:  
a magneto-optical garnet substrate having a first surface and a second surface, the first and second surfaces being coated with an anti-reflection material;

a first wire grid structure formed on the first surface, the first wire grid structure comprising a dielectric layer sandwiched between two metallic layers, the first wire grid structure being adapted to suppress reflection of rejected polarization; and

a second wire grid structure formed on the second surface and rotated an angle with respect to the first wire grid structure.

17. (original) The integrated optical isolator of claim 16, wherein the first wire grid structure comprises a plurality of substantially parallel grid elements, each grid element comprising a dielectric material sandwiched between two metallic materials.

18. (original) The integrated optical isolator of claim 17, wherein the metallic materials are selected from the group consisting of Al, Au, Cr, Ir, Mo, Ni, Os, Pt, Rh, and W.

19. (original) The integrated optical isolator of claim 17, wherein the dielectric material is selected from the group consisting of Si, SiO<sub>2</sub>, and GaAs.

20. (currently amended) A wire grid polarizer, comprising:  
a substrate which is transparent at a selected wavelength; and  
an anti-reflective wire grid structure formed on a surface of the substrate, the anti-reflective wire grid structure comprising a dielectric layer sandwiched between two metallic layers, the dielectric and metallic layers acting in concert to suppress reflection of rejected polarization.

21. (original) The wire grid polarizer of claim 20, wherein the surface of the substrate on which the anti-reflective wire grid structure is formed is coated with an anti-reflective material.

22. (original) The wire grid polarizer of claim 20, wherein the anti-reflective wire grid structure comprises a plurality of substantially parallel grid elements, each grid element comprising a dielectric material sandwiched between two metallic materials.

23. (original) The wire grid polarizer of claim 22, wherein the metallic materials are selected from the group consisting of Al, Au, Cr, Ir, Mo, Ni, Os, Pt, Rh, and W.

24. (original) The wire grid polarizer of claim 24, wherein the dielectric material is selected from the group consisting of Si, SiO<sub>2</sub>, and GaAs.

25. (new) The wire grid polarizer of claim 20, wherein the substrate is made of a magneto-optical garnet material.